

# DSR1M

## Surface Mount General Purpose Silicon Rectifiers

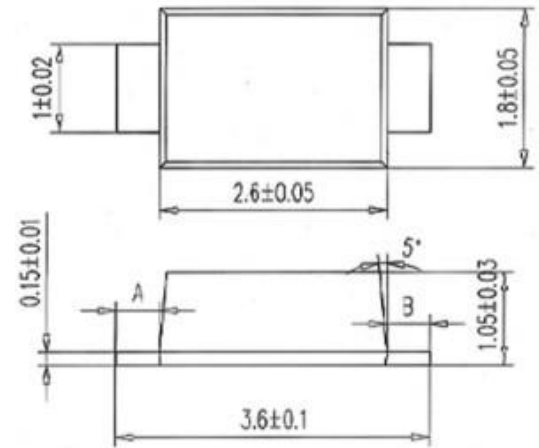
### Forward Current - 1 A

#### FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Ideal for automated placement
- Lead free in comply with EU RoHS 2011/65/EU directives

#### MECHANICAL DATA

- Case: SOD-123FL
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 14mg



#### Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

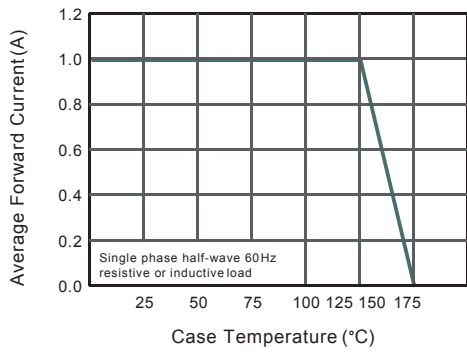
Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	DSR1M	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	1000	V
Maximum RMS voltage	$V_{RMS}$	700	V
Maximum DC Blocking Voltage	$V_{DC}$	1000	V
Maximum Average Forward Rectified Current at $T_c = 125^\circ\text{C}$	$I_{F(AV)}$	1	A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	$I_{FSM}$	25	A
Maximum Instantaneous Forward Voltage at 1 A	$V_F$	1.1	V
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at Rated DC Blocking Voltage $T_a = 125^\circ\text{C}$	$I_R$	5 50	$\mu\text{A}$
Typical Junction Capacitance <sup>(1)</sup>	$C_j$	11	pF
Typical Thermal Resistance <sup>(2)</sup>	$R_{\theta JA}$	90	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 ~ +150	$^\circ\text{C}$

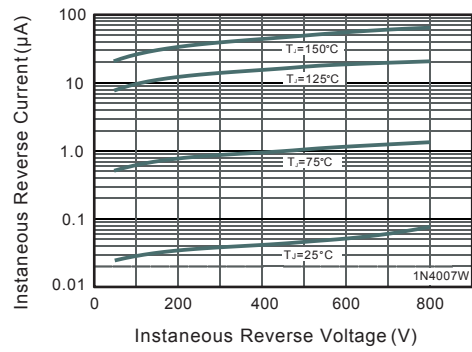
(1) Measured at 1 MHz and applied reverse voltage of 4 V<sub>DC</sub>

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

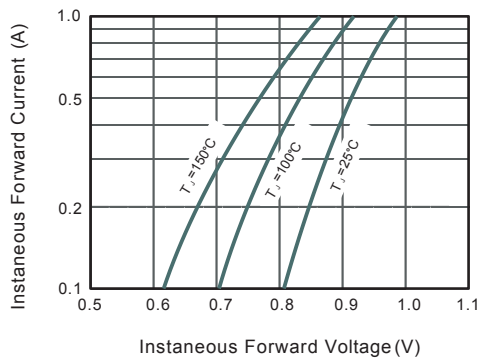
**Fig.1 Forward Current Derating Curve**



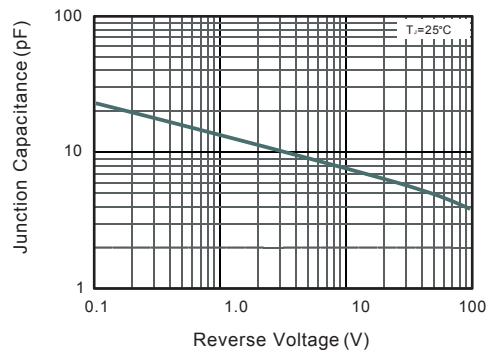
**Fig.2 Typical Instaneous Reverse Characteristics**



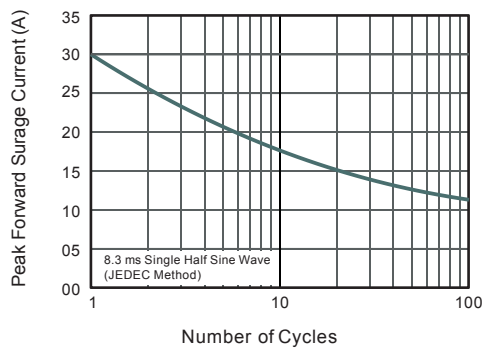
**Fig.3 Typical Forward Characteristic**



**Fig.4 Typical Junction Capacitance**



**Fig.5 Maximum Non-Repetitive Peak Forward Surge Current**



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[>>YONGYUTAI\(永裕泰\)](#)